

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	10	702/84.ccls. and measur\$4 with resistance and manufactur\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/18 13:42
L2	8	702/84.ccls. and measur\$4 with resistance and manufactur\$4 and adjust\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/18 13:43
L3	1	702/84.ccls. and measur\$4 with resistance and manufactur\$4 and adjust\$3 with resistance	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/18 13:43
L4	1	702/84.ccls. and measur\$4 with resistance and manufactur\$4 and adjust\$3 with resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/18 13:43
L5	0	702/81.ccls. and measur\$4 with resistance and manufactur\$4 and adjust\$3 with resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/18 13:43
L6	0	702/81.ccls. and measur\$4 with resistance and manufactur\$4 and adjust\$3 with resist\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/18 13:43
L7	0	702/82.ccls. and measur\$4 with resistance and manufactur\$4 and adjust\$3 with resist\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/18 13:44
L8	0	702/83.ccls. and measur\$4 with resistance and manufactur\$4 and adjust\$3 with resist\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/18 13:44
L9	9	324/763.ccls. and measur\$4 with resistance and manufactur\$4 and adjust\$3 with resist\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/18 13:44
L10	21	324/765.ccls. and measur\$4 with resistance and manufactur\$4 and adjust\$3 with resist\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/18 13:45
S1	0	measur\$4 with resistance with wafer with manufactur\$4 same distribution	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/17 13:42
S2	62	measur\$4 with resistance with wafer with manufactur\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/20 14:20

S3	10	measur\$4 with resistance with wafer with manufactur\$4 and resistance with design	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/20 14:21
S4	5	measur\$4 with resistance with wafer with manufactur\$4 and resistance with design and adjust\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/20 14:22
S5	4	measur\$4 with resistance with wafer with manufactur\$4 and resistance with design and adjust\$4 with resistance	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/20 14:27
S6	19	measur\$4 with resistance with wafer and resistance with design and adjust\$4 with resistance	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/20 14:27
S7	16	measur\$4 with resistance with wafer and resistance with design and adjust\$4 with resistance and manufactur\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/20 14:33
S8	21	measur\$4 with resistance and resistance with design and adjust\$4 with resistance and manufactur\$4 with wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 11:41
S9	8	measur\$4 with resistance and resistance with design and adjust\$4 with resistance and manufactur\$4 with wafer and offset	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/20 16:50
S10	0	resistance near distribution and resistance with design and offset and adjust with resistance and manufactur\$4 with wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/20 16:50
S11	0	resistance near distribution and resistance with design and offset and adjust with resistance and manufactur\$4 and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/20 16:50
S12	5	resistance with distribution and resistance with design and offset and adjust with resistance and manufactur\$4 and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/20 16:52
S13	20	resistance with distribution and offset and adjust with resistance and manufactur\$4 and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/20 17:35
S14	33	resistance with distribution and offset and (vary variable varying varied) with resist\$4 and manufactur\$4 and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/20 17:40

S15	10	resistance with distribution and offset and (vary variable varying varied) near resist\$4 and manufactur\$4 and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/20 17:44
S16	196	resistance with distribution and offset and (chang\$4 increas\$4 decreas\$4) near resist\$4 and manufactur\$4 and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/20 17:45
S17	7	resistance with distribution and offset near value and (chang\$4 increas\$4 decreas\$4) near resist\$4 and manufactur\$4 and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/20 17:45
S18	0	measur\$4 with resistance with (line lot manufactur\$4) with wafer and distribution near value and offset near value	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 11:42
S19	0	measur\$4 with resistance with (line lot manufactur\$4) with wafer and distribution and offset near value	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 11:42
S20	0	measur\$4 with resistance with wafer and distribution and offset near value	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 11:42
S21	15	measur\$4 with resistance and distribution and offset near value and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 11:43
S22	15	measur\$4 with resistance and distribution and offset near value and wafer and (lot line manufactur\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 11:57
S23	26	measur\$4 with resistance and offset near value and wafer and (lot line manufactur\$3) and (adjust\$4 chang\$4 increas\$ decreas\$4) near resistance	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 11:57
S24	8	measur\$4 with resistance and offset near value and wafer and (lot line manufactur\$3) and (adjust\$4 chang\$4 increas\$ decreas\$4) near resistance with offset	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 11:59
S25	12	measur\$4 with resistance and offset near value and wafer and (lot line manufactur\$3) and (adjust\$4 chang\$4 increas\$ decreas\$4) near resistance same offset	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 13:06

S26	3	measur\$4 near resistance with wafer with manufactur\$4 with line	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 13:06
S27	23	measur\$4 near resistance with wafer with manufactur\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 13:07
S28	1	measur\$4 near resistance with wafer with manufactur\$4 and offset	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 13:07
S29	4	measur\$4 near resistance with wafer with manufactur\$4 and (adjust\$4 increas\$4 decreas\$4) near resistance	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 13:26
S30	0	measur\$4 near resistance with wafer with manufactur\$4 and potentiometer	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 13:12
S31	0	measur\$4 near resistance with wafer with manufactur\$4 and variable near resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 13:13
S32	1817933	measur\$4 near resistance with wafer with manufactur\$4 and var\$5near resist\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 13:13
S33	0	measur\$4 near resistance with wafer with manufactur\$4 and var\$5 near resist\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 13:13
S34	0	measur\$4 near resistance and compar\$4 with resistance with design and (adjust\$4 vary varying variable chang\$4) with resistance with offset	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 13:27
S35	60	measur\$4 near resistance and compar\$4 with resistance and (adjust\$4 vary varying variable chang\$4) with resistance with offset	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 13:27
S36	39	measur\$4 near resistance and compar\$4 with resistance and (adjust\$4 vary varying variable chang\$4) with resistance with offset and manufactur\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 13:29

S37	2	measur\$4 near resistance with potentiometer and compar\$4 with resistance and (adjust\$4 vary varying variable chang\$4) with resistance with offset and manufactur\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 13:32
S38	3	measur\$4 with resistance with potentiometer and compar\$4 with resistance and (adjust\$4 vary varying variable chang\$4) with resistance with offset and manufactur\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 13:32
S39	5	measur\$4 with resistance with potentiometer and compar\$4 with resistance and (adjust\$4 vary varying variable chang\$4) with resistance with offset	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 13:34
S40	36	measur\$4 with resistance with potentiometer and compar\$4 with resistance and (adjust\$4 vary varying variable chang\$4) with resistance and manufactur\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 13:36
S41	18	manufactur\$4 with potentiometer and measur\$4 with resistance and compar\$4 with resistance and (adjust\$4 vary varying varied chang\$4 increas\$4 decreas\$4) near resistance	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 13:39
S42	18	manufactur\$4 with potentiometer and measur\$4 with resistance and compar\$4 with resistance and (adjust\$4 vary varying varied chang\$4 increas\$4 decreas\$4) near (resistor resistance)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 13:40
S43	19	manufactur\$4 with potentiometer and measur\$4 with resistance and compar\$4 with resistance and (adjust\$4 vary varying varied chang\$4 increas\$4 decreas\$4) near (resistor resistance potentiometer)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 13:45
S44	6	manufactur\$4 with resistor near circuit and measur\$4 with resistance and compar\$4 with resistance and (adjust\$4 vary varying varied chang\$4 increas\$4 decreas\$4) near (resistor resistance potentiometer)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 13:46

S45	301	manufactur\$4 with resistor and measur\$4 with resistance and compar\$4 with resistance and (adjust\$4 vary varying varied chang\$4 increas\$4 decreas\$4) near (resistor resistance potentiometer)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 13:47
S46	18	manufactur\$4 with resistor with chip and measur\$4 with resistance and compar\$4 with resistance and (adjust\$4 vary varying varied chang\$4 increas\$4 decreas\$4) near (resistor resistance potentiometer)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 13:57
S47	13	test\$4 with (potentiometer resistors) with manufactur\$4 and measur\$4 with resistance and compar\$4 with resistance and (adjust\$4 increas\$3 decreas\$3 chang\$3 vary varying variable) with (resistor resistance)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 14:22
S48	10	test\$4 with (potentiometer resistors) with manufactur\$4 and measur\$4 with resistance and compar\$4 with resistance and (adjust\$4 increas\$3 decreas\$3 vary varying variable) with (resistor resistance)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 15:00
S49	391	resistance with manufactur\$3 with line and test\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 15:00
S50	30	measur\$4 with resistance with manufactur\$3 with line and test\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 15:01
S51	5	measur\$4 with resistance with manufactur\$3 near line and test\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 15:01
S52	4	measur\$4 with resistance with manufactur\$3 near line and test\$3 and (adjust\$4 increas\$3 decreas\$3 vary varying varied) with (resistance resistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 16:21
S53	21	measur\$4 with resistance with wafer with (line lot manufactur\$3) and compar\$4 with resistance and (adjust\$4 increas\$4 decreas\$4) with resistance	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 16:36

S54	1	measur\$4 with resistance with wafer with (line lot manufactur\$3) and compar\$4 with resistance and (amodify\$3 vary\$4) with resistance	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 16:37
S55	2	measur\$4 with resistance with wafer with (line lot manufactur\$3) and compar\$4 with resistance and (modify\$3 vary\$4) with resistance	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 16:44
S56	932	(adjust\$3 modify\$3) with (potentiometer (variable near resistor)) with offset	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 16:45
S57	129	(adjust\$3 modify\$3) near (potentiometer (variable near resistor)) with offset and manufactur\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 16:45
S58	2	(adjust\$3 modify\$3) near (potentiometer (variable near resistor)) with offset and manufactur\$4 and compar\$4 and measur\$4 near resistance	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 16:46
S59	4	(adjust\$3 modify\$3) near (potentiometer (variable near resistor)) with offset and manufactur\$4 and measur\$4 near resistance	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 16:46
S60	21	(adjust\$3 modify\$3) near (potentiometer (variable near resistor)) and compar\$4 with resistance and manufactur\$4 and measur\$4 near resistance	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/21 16:46
S61	1	measur\$4 with resistance with wafer same manufactur\$4 same distribution	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/17 14:14
S62	11	measur\$4 with resistance with wafer same test\$4 same distribution	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/17 14:15
S63	0	measur\$4 with resistance with wafer same test\$4 and distribution with resistance and offset	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/17 14:15
S64	11	measur\$4 with resistance with wafer and distribution with resistance and offset	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/17 14:18

S65	3	measur\$4 with resistance with wafer and distribution with resistance and offset and resistance with (design model)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/17 14:18
S66	5	measur\$4 with resistance with wafer and distribution with resistance and correlat\$3 and resistance with (design model)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/17 14:24
S67	15	manufactur\$3 with (wafer semiconductor) and measur\$4 with resistance with wafer and correlat\$4 same (design model)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/17 14:26
S68	2	manufactur\$3 with (wafer semiconductor) and measur\$4 with resistance with wafer and correlat\$4 same (design model) and distribution same resistance	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/17 14:27
S69	18	manufactur\$3 with (wafer semiconductor) and measur\$4 with resistance with wafer and distribution same resistance and adjust\$4 with resistance and (model design\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/18 13:42